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Letter

Room-Temperature Magnetic Order in Air-Stable Ultrathin Iron Oxide

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Supporting Information

ABSTRACT: Manual assembly of atomically thin materials into heterostructures with desirable electronic properties is an approach that holds great promise. Despite the rapid expansion of the family of ultrathin materials, stackable and stable ferro/ferri magnets that are functional at room temperature are still out of reach. We report the growth of air-stable, transferable ultrathin iron oxide crystals that exhibit magnetic order at room temperature. These crystals require no passivation and can be prepared by scalable and cost-effective chemical vapor deposition. We demonstrate that the bonding between iron oxide and its growth substrate is van der Waals-like, enabling us to remove the crystals from their growth substrate and prepare iron oxide/graphene heterostructures.



KEYWORDS: Iron oxide, room-temperature magnetism, van der Waals heterostructure, ultrathin

here is great interest in using mechanical stacking,^{1,2} rather than epitaxial materials growth, to assemble heterostructures of materials which exhibit diverse, intriguing properties such as valley polarization,³ ferroelectricity,⁴ superconductivity,⁵ and charge-density waves.^{6,7} Efforts have been made to create stackable magnetic materials through engineering of defects, but only local magnetism has been achieved.^{8–10} The recent discoveries of layered materials supporting intrinsic ferromagnetism have made stacked spintronic heterostructures realistic.^{11–17} However, manual assembly of multilayer devices with these ferromagnets under ambient conditions remains challenging due to material sensitivity to environmental degradation, and magnetic order at room temperature is rare in van der Waals materials. Here, we show synthesis of ultrathin crystals of ε -Fe₂O₃ by scalable ambient pressure chemical vapor deposition (CVD), finding ready formation on both silicon dioxide and mica substrates. Electron microscopy and Raman spectroscopy measurements confirm that the crystals are pure ε -Fe₂O₃, with no detectable amounts of the more common α -Fe₂O₃ and γ -Fe₂O₃ phases, for crystals thinner than approximately 100 nm. Furthermore, the magneto-optical Kerr effect (MOKE) magnetometry of individual crystals shows that they are magnetically stable, with coercive fields of hundreds of mT. We observe robust hysteresis even in crystals as thin as 7 nm at room temperature in atmosphere. These samples of ultrathin ε -Fe₂O₃ can be readily transferred from growth

substrates in aqueous solutions at ambient conditions to arbitrary substrates without any visible structural changes. Finally, despite the fact that these CVD-grown ultrathin ε -Fe₂O₃ crystals are not van der Waals materials, their atomically sharp surfaces and nanoscale thicknesses allow them to be easily integrated with two-dimensional (2D) materials such as graphene, thereby eliminating the lattice mismatching constraints for design of functional heterostructures. This CVD growth, manipulation, and magnetic study of comparatively large individual crystals is complementary to recent successes in liquid-phase exfoliation of ensembles of nanoscale ultrathin hematite crystals.¹⁸

 ε -Fe₂O₃ has an orthorhombic structure with lattice constants a = 5.072 Å, b = 8.736 Å, c = 9.418 Å and belongs to the space group of $Pna2_1$.¹⁹ There are four independent crystallographically nonequivalent iron sites, denoted as Fe_A, Fe_B, Fe_C, and Fe_D, occupying the center of either the octahedron or tetrahedron formed by surrounding oxygen atoms (Figure 1a). We grow samples with standard CVD techniques (see Methods for growth details in the SI). Ultrathin crystals of iron oxide with lateral size of $\approx 10 \ \mu$ m readily form using this procedure and are apparent in optical micrographs (Figure 1b–d). All crystals

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Figure 1. Crystal structure and optical images of ε -Fe₂O₃. (a) Nonlayered ε -Fe₂O₃ has an orthorhombic structure with a = 5.072 Å, b = 8.736 Å, and c = 9.418 Å. There are four independent iron sites, denoted as Fe_A, Fe_B, Fe_C, and Fe_D. Inset: Individual octahedron formed by one center iron atom and six surrounding oxygen atoms, representing the cation coordination of Fe_A, Fe_B, Fe_C, and an individual tetrahedron formed by one center iron atom and four surrounding oxygen atoms, representing the cation coordination of Fe_D. (b–d) Optical images of ε -Fe₂O₃ crystals grown on mica by CVD. Ultrathin crystals with a lateral size of many μ m can be easily found in each batch of growth, as indicated by the red arrows. The out-of-plane growth direction is [001]. Grain structure of the crystals is discussed below.



Figure 2. Characterization of ε -Fe₂O₃. (a, b) Two representative ultrathin ε -Fe₂O₃ crystals with hexagonal and triangular shapes grown on a mica substrate. The well-defined shapes indicate high crystal quality. Scale bars are 5 μ m. (c, d) AFM thickness measurements for crystals in (a) and (b). The thicknesses are 5.8 and 7.5 nm, respectively. (e, f) The corresponding spatially resolved Raman mapping for crystals in (a) and (b). The intensities are the sum of signals between 100 and 200 cm⁻¹, normalized by the Raman peak of mica substrate. The homogeneous intensity distributions show that the ε -Fe₂O₃ phase is uniformly distributed within the crystals. (g) Raman spectra collected from ε -Fe₂O₃ and α -Fe₂O₃ crystals on silicon dioxide. The four characteristic peaks between 100 and 200 cm⁻¹ represent the first-order phonon modes, namely M1–M4, of ε -Fe₂O₃ polycrystalline flake transferred from the mica substrate. At least three individual grains, marked by I, II, and III are present in this flake. GBs are highlighted by red dotted lines. Inset: Zoom-in image of a GB. (i) Electron diffraction patterns from three grains in (h), which can also be indexed to the orthorhombic symmetry of ε -Fe₂O₃ in the [001] zone axis. The angles between grains I and II and grains II and III are about 56° and 45°, respectively.

exhibit well-defined shapes with sharp edges, showing clear evidence of high crystallinity.

Figure 2a,b shows atomic force microscopy (AFM) images of two representative crystals with thicknesses of \approx 5.8 nm and \approx 7.5 nm (Figure 2c,d). The thinnest crystal we have measured is \approx 5.1 nm, which is only five unit-cells thick. The ultrathin Fe₂O₃ crystals have atomically smooth surfaces and uniform thicknesses, with a standard deviation roughness <0.5 nm. Micro-Raman measurements of these samples (Figure 2g) show four peaks between 100 and 200 cm⁻¹, which are the characteristic first-order phonon vibration modes M1–M4 of ε -Fe₂O₃, in agreement with previous literature.²⁰ In comparison, the most stable bulk phase α -Fe₂O₃ has no Raman active modes in this range. Full spectrum comparison can be found in Figure S1. Spatially resolved Raman mappings (Figure 2e,f) further suggest uniformity within individual crystals. No detectable second phase was observed.

We employed transmission electron microscopy (TEM) to gain further structural insight of the as-synthesized ultrathin Fe_2O_3 . Figure 2h is a dark-field TEM image of an ultrathin Fe_2O_3 polycrystalline flake where grain boundaries (GBs) can be visualized. The GBs are highlighted by red dotted lines, and

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Figure 3. Room-temperature magnetic order in nanoscale thickness ε -Fe₂O₃. (a–d) MOKE hysteresis loops obtained from crystals with varying thicknesses from 7.5 to 50.1 nm, demonstrating magnetic order with symmetric hysteresis and coercive fields \approx 300 mT. (e) The amplitude of the Kerr effect plotted against the thickness of the crystals measured by AFM, showing no correlation. (f) The coercive field plotted as a function of thickness, showing no obvious trend. Coercive fields and amplitudes are measured from the hysteresis loops by fitting the magnetic transitions to error functions. Backgrounds were removed from these hysteresis curves according to the procedure described in Figure S5. (g) The coercive field plotted as a function of flake area, showing no obvious trend.

a detail of a GB is displayed in the inset of Figure 2h. At least three grains, marked by I, II, and III, are present in this flake. The electron diffraction patterns (Figure 2i) from a randomly selected area in each grain can be indexed to the orthorhombic symmetry of ε -Fe₂O₃ in the [001] zone axis, consistent with the results from Raman spectroscopy (see SI Figure S2 for detailed phase index procedure). Although the three grains have the same out-of-plane growth direction, within the plane they orient differently, as indicated by the g (020) vectors. The angle between grains I and grain II is about 56° and between grains II and grain III is about 45°.

In addition to examining multiple randomly transferred crystals, we performed TEM and Raman analysis on the same thicker crystal ($\approx 100 \text{ nm}$) by breaking it into two halves. The resulted TEM index matches well with that of Raman analysis (characteristic peaks between 100 and 200 cm⁻¹), confirming that Raman spectroscopy is an accurate and rapid way to identify ultrathin ε -Fe₂O₃. In total, we have checked 23 crystals with thicknesses ranging from 5.1 to 260 nm. Of these, 22 crystals show the ε phase (see SI Figure S3).

To provide more insights about the growth mechanism, we analyzed the ε -Fe₂O₃ flakes by time-of-flight secondary ion mass spectrometry (TOF-SIMS). The chemical mapping in Figure S4 reveals that the flakes are laterally uniform with a clear contrast between the flakes and mica substrate. A higher Cl signal in the flake regions (Figure S4b) indicates the preferential adsorption of Cl. In-depth analysis further confirms that Cl is present on the surface of the flake, while there is no noticeable Cl inside of the ε -Fe₂O₃ flake. This TOF-SIMS analysis provides evidence that the absorption of Cl might be one of the reasons why we can achieve highly anisotropic ultrathin growth for ε -Fe₂O₃.

We next probe the magnetic properties of these ultrathin ε -Fe₂O₃ crystals with longitudinal MOKE measurement at room temperature (295 K). The measurement geometry is shown in the inset of Figure 3a, and further details of the measurement and data processing are described in Methods. Figure 3a-d show typical hysteresis loops of Kerr rotation $\theta_{\rm K}$ as

a function of magnetic field, B, for samples with thickness ranging from 7.5 to 50.1 nm. These loops clearly show roomtemperature magnetic order in ultrathin ε -Fe₂O₃ with welldefined transitions and coercive fields of hundreds of mT. Noting the difference in the amplitude of the Kerr effect, in particular between the 7.5 and 15 nm-thick samples (Figure 3a,c), we investigated 15 other crystals with different thicknesses to check for an influence of thickness on magnetic properties. Of these, all show a similar room temperature switching behavior, with a mean coercive field of 290 mT and a standard deviation of 80 mT. These results agree well with previous measurements of nanoparticles 21,22 and thin films of $\varepsilon\text{-Fe}_2\text{O}_3.^{23}$ To check the robustness of the magnetic properties of our samples at room temperature, we plot the coercive field and the amplitude of the magnetic transitions as a function of sample thickness, as measured by AFM. We find that neither the amplitude of the Kerr effect (Figure 3e) nor the coercive field (Figure 3f) correlates with sample thickness. This absence of correlation confirms the robustness of magnetic order of this material even in ultrathin thickness. This observation is in contrast with other magnetic samples. For example, magnetite (Fe₃O₄) films^{24,25} and nanoparticles²⁶ show a strong dependence of coercive field on sample dimensions. In this regard, our data on ultrathin ε -Fe₂O₃ suggest that it has a promising potential in ultracompact information storage applications. We also plot the coercive field as a function of flake area in Figure 3g, which also shows no correlation. These observations suggest that the coercive field is set by local properties within the ε -Fe₂O₃, rather than by any thickness tuning of exchange processes or by geometric anisotropy.

Electronic transport measurements (see Figures S6 and S7) show that the material is highly resistive, with a room-temperature resistivity on the order of 100 Ω ·m. This is comparable to expectations for the related oxide, hematite,^{27,28} and implies high sample quality through the lack of doping from vacancies or impurities.

One distinctive advantage of ultrathin ε -Fe₂O₃ is that these crystals have exceptional stability. Figure 4a is an AFM image



Figure 4. Stability and transferability of ultrathin ε -Fe₂O₃. (a) AFM image of a crystal stored under ambient conditions for over 3 months. No obvious voids or morphology changes can be observed. Scale bar: 2 μ m. (b) Height profile analysis across the whole crystal indicates that the surface is highly smooth, with a standard deviation roughness of 0.28 nm, and edges are sharp without any signs of degradation. (c) Scheme of transferring ultrathin ε -Fe₂O₃ crystals from mica growth substrate and building an ε -Fe₂O₃/graphene heterostructure. The monolayer CVD-grown graphene film is on a SiO₂/Si substrate. Scale bar: 2 μ m.

of a crystal stored in ambient condition (T = 24.0 °C, RH = 39%) for over 3 months. No obvious voids or morphology changes were observed. Height profile analyses across the whole sample (Figure 4b) reveals that the crystal still has an atomically smooth surface with a standard deviation roughness of 0.28 nm and sharp edges. Therefore, it is not likely that these ultrathin ε -Fe₂O₃ crystals will be further degraded, demonstrating extraordinary stability compared to other nanoscale magnetic materials reported so far. Remarkably, ultrathin ε -Fe₂O₃ can be transferred easily from the growth substrate like van der Waals layered materials. Taking advantage of its stability, we prepared a ε -Fe₂O₃/graphene film heterostructure through a water-assisted polycarbonate transfer method, where no harsh chemical etchants were involved. The transfer scheme and outcome are illustrated in Figure 4c. The well-defined and intact flake after transfer clearly demonstrates the bonding between *e*-Fe₂O₃ and its growth substrate is noncovalent, thereby allowing ultrathin ε -Fe₂O₃ to be handled as a van der Waals material for building different types of heterostructure devices.

In summary, ultrathin ε -Fe₂O₃ can be synthesized via a scalable ambient CVD technique. MOKE measurements on individual crystals clearly show that ultrathin ε -Fe₂O₃ is magnetically ordered at room temperature with coercive fields of 200–400 mT and sharp magnetic transitions, even down to 7.5 nm thickness. Moreover, ultrathin ε -Fe₂O₃ will not degrade under ambient conditions for months. We further demonstrate that these crystals can be transferred from a growth substrate and integrated into a ε -Fe₂O₃/graphene heterostructure through well-established methods developed for 2D materials at ambient conditions. Thanks to these useful and unique properties, ultrathin ε -Fe₂O₃ will be a promising and

distinctive platform to explore magnetism in the nanoscale limit. It is envisioned that new conceptual devices with novel spin functionalities could be developed through heterostructure engineering with other layered materials.

ASSOCIATED CONTENT

Supporting Information

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acs.nanolett.9b00905.

Materials and methods and Figures S1-S7 (PDF)

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Author Contributions

¹J.Y. and A.B. contributed equally. J.Y. and J.L. conceived the idea and designed the experiments. J.Y., S.P., and Q.F. conducted the materials growth and Raman and AFM characterization. A.B. and S.C. performed the MOKE measurements. A.B. processed and analyzed the MOKE data. H.G. carried out the TEM characterization and phase index from electron diffraction patterns. X.Z. and D.N. handled the device fabrication magnetotransport measurements. T.T. performed TOF-SIMS analysis. All authors wrote the manuscript and discussed the results at all stages. All authors have given approval to the final version of the manuscript.

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Notes

The authors declare no competing financial interest.

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